

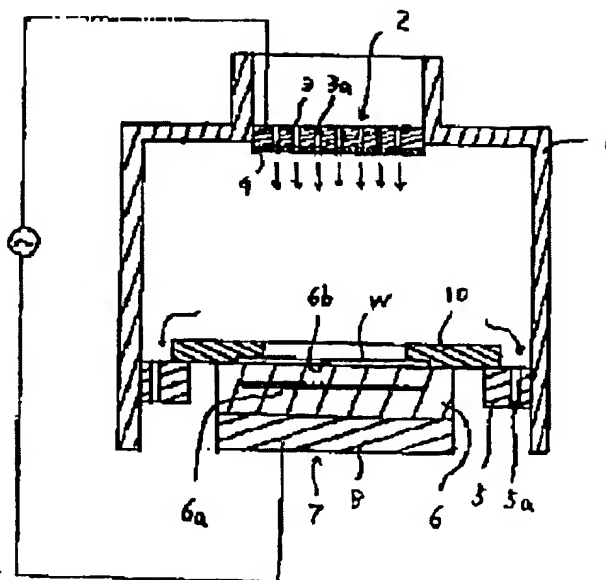
## PLASMA GENERATING ELECTRODE

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**Classification:**  
- **International:** H05H1/46; C01B31/06; C23C16/50; C23F4/00;  
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- **European:**  
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### Abstract of JP11251093

**PROBLEM TO BE SOLVED:** To provide a plasma generating electrode that is hardly corroded even if it is exposed to plasma under a corrosive halogen gas, and can generate good quality plasma for a long time without giving adverse effect such as particles on a semiconductor wafer or the like.

**SOLUTION:** A plasma generating electrode 2 is composed by covering at least a part that is located on a conductive base body 3 formed from any of silicon(Si, carbon(C) and silicon carbide and is exposed to plasma under a corrosive halogen gas with a hard carbon film 4 formed from a material such as diamond-like carbon having an amorphous structure or a crystalline structure or diamond.



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